

**IN THE SPECIFICATION:**

Please delete the second paragraph on page 31 of the specification and replace it with the following:

As shown in Fig. 416, the temperature during high-temperature annealing at which the size of the void defects 3 shrinks and the void defects are eliminated (the minimum temperature required to eliminate void defects) rises in proportion to the initial oxygen concentration, and the size of the void defects 3 shrinks suddenly at around 1300°C, so it is believed that a void defect elimination effect appears in the vicinity of 1300°C. If the initial oxygen concentration is  $10 \times 10^{17}$  (atoms/cc) (ASTM F121-79), then the void defects 3 begin to shrink when the temperature during high-temperature annealing is at least 1280°C. Therefore, if the oxygen concentration is lower, the void defect elimination effect should appear at about 1280°C.